# RENESAS BCR10CM-12LA

Triac

Medium Power Use

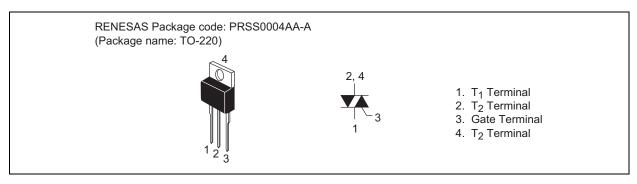
REJ03G0296-0300 Rev.3.00 Nov 30, 2007

### Features

- $I_{T (RMS)} : 10 A$
- V<sub>DRM</sub> : 600 V
- I<sub>FGTI</sub>, I<sub>RGTI</sub>, I<sub>RGT III</sub>: 30 mA (20 mA)<sup>Note6</sup>

# Outline

- Non-Insulated Type
- Planar Passivation Type



# Applications

Contactless AC switch, light dimmer, electronic flasher unit, control of household equipment such as TV sets, stereo systems, refrigerator, washing machine, infrared kotatsu, carpet, electric fan, solenoid driver, small motor control, copying machine, electric tool, electric heater control, and other general purpose control applications

# **Maximum Ratings**

Parameter	Symbol	Voltage class	Unit	
Faiameter	Symbol	12		
Repetitive peak off-state voltage <sup>Note1</sup>	V <sub>DRM</sub>	600	V	
Non-repetitive peak off-state voltage <sup>Note1</sup>	V <sub>DSM</sub>	720	V	

### BCR10CM-12LA

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	I <sub>T (RMS)</sub>	10	A	Commercial frequency, sine full wave $360^{\circ}$ conduction, Tc = $103^{\circ}C^{Note3}$
Surge on-state current	I <sub>TSM</sub>	100	A	60Hz sinewave 1 full cycle, peak value, non-repetitive
I <sup>2</sup> t for fusing	l <sup>2</sup> t	41.6	A <sup>2</sup> s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	P <sub>GM</sub>	5	W	
Average gate power dissipation	P <sub>G (AV)</sub>	0.5	W	
Peak gate voltage	V <sub>GM</sub>	10	V	
Peak gate current	I <sub>GM</sub>	2	А	
Junction temperature	Tj	- 40 to +125	°C	
Storage temperature	Tstg	- 40 to +125	°C	
Mass	—	2.0	g	Typical value

Notes: 1. Gate open.

### **Electrical Characteristics**

Parameter		Symbol	Min.	Тур.	Max.	Unit	Test conditions
Repetitive peak off-state cur	rent	I <sub>DRM</sub>	_		2.0	mA	Tj = 125°C, V <sub>DRM</sub> applied
On-state voltage		V <sub>TM</sub>	_	—	1.5	V	Tc = 25°C, $I_{TM}$ = 15 A, Instantaneous measurement
Gate trigger voltage <sup>Note2</sup>	Ι	$V_{FGTI}$	_		1.5	V	$Tj = 25^{\circ}C, V_D = 6 V, R_L = 6 \Omega,$
	II	V <sub>RGTI</sub>	_	—	1.5	V	R <sub>G</sub> = 330 Ω
	III	V <sub>RGTIII</sub>	_		1.5	V	
Gate trigger current <sup>Note2</sup>	Ι	I <sub>FGTI</sub>	_		30 <sup>Note6</sup>	mA	$Tj = 25^{\circ}C, V_D = 6 V, R_L = 6 \Omega,$
	II	I <sub>RGTI</sub>	—	—	30 <sup>Note6</sup>	mA	$R_G = 330 \Omega$
	III	I <sub>RGTIII</sub>	_		30 <sup>Note6</sup>	mA	
Gate non-trigger voltage		$V_{GD}$	0.2		_	V	$Tj = 125^{\circ}C, V_{D} = 1/2 V_{DRM}$
Thermal resistance		R <sub>th (j-c)</sub>	_		1.8	°C/W	Junction to case <sup>Note3 Note4</sup>
Critical-rate of rise of off-stat commutating voltage <sup>Note5</sup>	te	(dv/dt)c	10	—	—	V/µs	Tj = 125°C

Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

3. Case temperature is measured at the  $T_2 \mbox{ tab } 1.5 \mbox{ mm}$  away from the molded case.

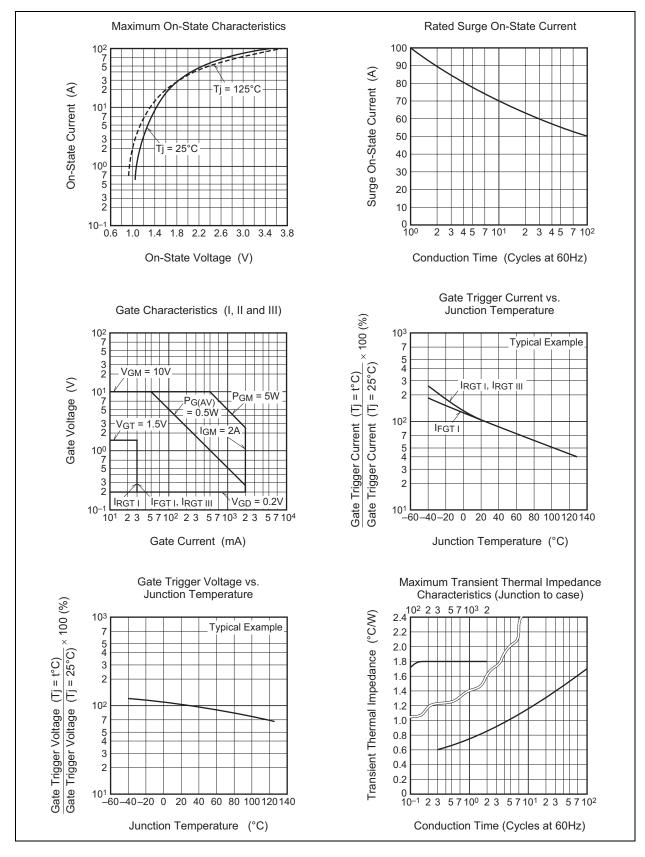
4. The contact thermal resistance  $R_{th\,(c\text{-}f)}$  in case of greasing is 1.0°C/W.

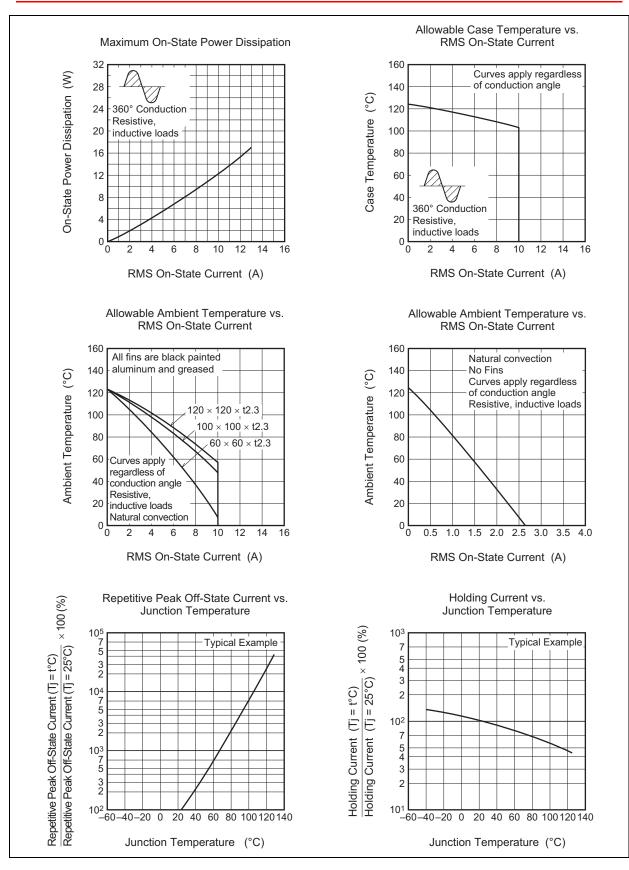
5. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

6. High sensitivity (I\_{GT}  $\leq 20$  mA) is also available. (I\_{GT} item: 1)

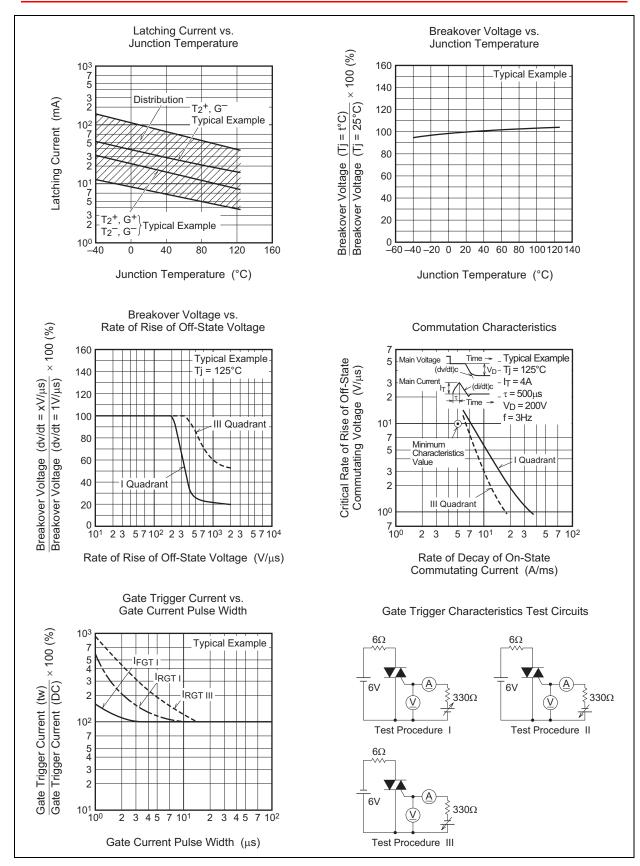
Test conditions	Commutating voltage and current waveforms (inductive load)		
1. Junction temperature Tj = 125°C	Supply Voltage → Time		
2. Rate of decay of on-state commutating current (di/dt)c = - 5.0 A/ms	Main Current → Time		
3. Peak off-state voltage $V_D = 400 \text{ V}$	Main Voltage → Time (dv/dt)c V <sub>D</sub>		

### **Performance Curves**



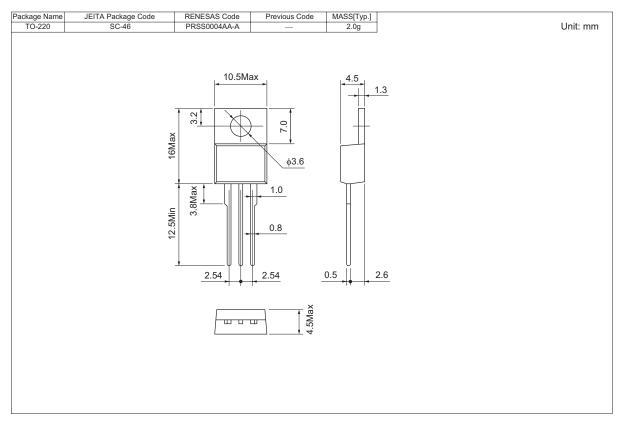


### REJ03G0296-0300 Rev.3.00 Nov 30, 2007 **RENESAS** Page 4 of 6



REJ03G0296-0300 Rev.3.00 Nov 30, 2007 **RENESAS** Page 5 of 6

# **Package Dimensions**



### Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Vinyl sack	100	Type name	BCR10CM-12LA
Lead form	Plastic Magazine (Tube)	50	Type name – Lead forming code	BCR10CM-12LA-A8

Note : Please confirm the specification about the shipping in detail.

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